RTG4 Two-Port Large SRAM Configuration User Guide



Introduction (Ask a Question)

The RTG4[™] Two-Port Large SRAM configurator helps to configure a Two-Port Large SRAM instance and define how the signals are connected.

A Two-Port Large SRAM allows write access on one port and read access on the other port (see the following figure). The core configurator cascades Large SRAM blocks automatically to create wide and deep memories by choosing the most efficient aspect ratio. It also handles the grounding of unused bits. The core configurator supports the generation of memories that have different Read and Write aspect ratios.

Two-Port Large SRAM is synchronous with read and write operations, setting up the addresses as well as writing and reading the data. The memory write and read operations are triggered at the rising edge of the clock. The address, data, write-enable, and read-enable inputs are registered.

An optional pipeline register is available at the read data port to improve the clock-to-out delay. When ECC is enabled, output flags are generated to indicate single-bit-correct and double-bit-detect.

For more information about Two-Port Large SRAM, refer to the RTG4 User Guide.

Figure 1. Two-Port Large SRAM Configurator

Optimized for 🔅 High Speed	C Low Power	T Initialize RAM for Simulation	-	Customize RAM Content	
Write Port	WD [17:0	1			
Depth: 1024	WADDR [9:0]				
Width: 18	WEN P				
I⊽ Single Clock					
ακ 🗄 于 🛶	>	[17:0] RD			
Read Port	REN	F Pipeline			
Denth 1024	BADDR [9:0]				
Width 18	RD_EN				
	RD_SRST_N				
Expose Write Byte Enables					
ECC: Disabled	ARST N				
	Control Million of Control of Con				

Table of Contents

Intr	oduction	1
1.	Using the RTG4 Two-Port Large SRAM	4
	1.1. Optimization for High Speed or Low Power	4
	1.2. Write Depth/Width and Read Depth/Width	4
	1.3. Single Clock (CLK) or Independent Write and Read Clocks (WCLK, RCLK)	4
	1.4. Write Enable (WEN)	4
	1.5. Read Enable (REN)	4
	1.6. Pipeline for Read Data Output	4
	1.7. Register Enable (RD_EN)	4
	1.8. Synchronous Reset (RD_SRST_N)	5
	1.9. Asynchronous Reset (ARST_N)	5
	1.10. Expose Write Byte Enables (WBYTE_EN)	5
	1.11. Error Correction Code (ECC)	5
	1.12. RD Register Truth Table	5
2.	Internal Configurator Connections	6
	2.1. WEN Connections	6
	2.2. REN Connections	6
	2.3. WD Connections	7
	2.4. RD Logic	7
	2.5. SB_CORRECT and DB_DETECT Logic	7
3.	Caveats for Two-Port Large SRAM Generation	8
4.	Supported Formats	9
	4.1. Intel HEX	9
	4.2. Motorola S-Record	9
	4.3. Write Port Width Alignment	10
5.	RAM Content Manager	17
	5.1 Opening and Using RAM Content Manager	17
	5.2. MEMFILE (RAM Content Manager Output File)	19
c		21
0.		∠1
7.	Parameters	22
8.	Revision History	25
Mic	ochip FPGA Support	26
Mic	ochip Information	26
	The Microchip Website	26
	Product Change Notification Service	26
	Customer Support	26
	Microchip Devices Code Protection Feature	26
	Legal Notice	27
	Trademarks	27



Quality Management System	28
Norldwide Sales and Service	29



1. Using the RTG4 Two-Port Large SRAM (Ask a Question)

This chapter describes the RTG4 Two-Port Large SRAM functions.

1.1 Optimization for High Speed or Low Power (Ask a Question)

Selecting High Speed results in a macro optimized for speed and area (width cascading).

Selecting Low Power results in a macro optimized for low power, but uses additional logic at the input and output (depth cascading). Performance for a low power optimized macro may be inferior to that of a macro optimized for speed.

1.2 Write Depth/Width and Read Depth/Width (Ask a Question)

The depth range for each port is 1-65536. The width range for each port is 1-7524.

The two ports can be independently configured for any depth and width. (Write Depth * Write Width) must equal (Read Depth * Read Width)

1.3 Single Clock (CLK) or Independent Write and Read Clocks (WCLK, RCLK) (Aska

Question)

The default configuration for Two-Port Large SRAM is a Single clock (CLK) to drive WCLK and RCLK with the same clock. Uncheck the Single clock check box to drive independent clocks (one each for Write and Read).

Click the up or down button next to the waveform of the clock signals to toggle the clock's active edge.

1.4 Write Enable (WEN) (Ask a Question)

Asserting WEN writes the data WD into the RAM at the address WADDR on the next rising edge of WCLK. Unchecking the WEN option ties the signal to the active state and removes it from the generated macro. Click the signal arrow (

) when available to toggle its polarity.

1.5 Read Enable (REN) (Ask a Question)

When there is no depth cascading, de-asserting REN holds the previous Read data (RD). When there is depth cascading, de-asserting REN generates zeros on RD. These different behaviors occur because the component's REN input is used to drive either the LSRAM block's A_REN input or the read-port block select input (A_BLK), depending on the cascading configuration.

Asserting REN reads the RAM at the read address RADDR onto the input of the RD register on the next rising edge of RCLK.

The default configuration for REN is unchecked, which ties the signal to the active state and removes it from the generated macro. Click the check box to insert that signal on the generated macro. Click the signal arrow (when available) to toggle its polarity.

1.6 Pipeline for Read Data Output (Ask a Question)

Click the Pipeline check box to enable pipelining for Read data (RD).

Turning off pipelining of Read data also disables the configuration options of the RD_EN, RD_SRST_N and ARST_N signals.

1.7 Register Enable (RD_EN) (Ask a Question)

The pipeline register for RD has an active high, enable input. The default configuration is to tie this signal to the active state and remove it from the generated macro. Click the signal's check box to insert that signal on the generated macro. Click the signal arrow (when available) to toggle its polarity.



1.8 Synchronous Reset (RD_SRST_N) (Ask a Question)

The pipeline register for RD has an active low, synchronous reset input. The default configuration is to tie this signal to the inactive state and remove it from the generated macro. Click the signal's check box to insert that signal on the generated macro. Click the signal arrow (when available) to toggle its polarity.

1.9 Asynchronous Reset (ARST_N) (Ask a Question)

The pipeline register for RD has an active low, asynchronous reset input. The default configuration is to tie this signal to the inactive state and remove it from the generated macro. Click the signal's check box to insert that signal on the generated macro. Click the signal arrow (when available) to toggle its polarity.

1.10 Expose Write Byte Enables (WBYTE_EN) (Ask a Question)

When enabled, write byte enables (WBYTE_EN) are available as a top-level bus. Each bit of WBYTE_EN enables writing to an individual byte of data. When ECC is enabled, the state of the WBYTE_EN bits should be identical for each LSRAM block.

1.11 Error Correction Code (ECC) (Ask a Question)

Three options are available for ECC:

- Disabled
- Pipelined
- Non-Pipelined

When ECC is disabled, each port can be configured to a width of 36 bits, 18 bits, or 9 bits. Alternatively, both ports can be configured to a 12-bit width.

When ECC is enabled (Pipelined or Non-Pipelined), both ports have word widths equal to 36 bits or 18 bits.

1.12 RD Register Truth Table (Ask a Question)

The following table describes the functionality of the control signals on the RD register.

ARST_N	RCLK	RD_EN	RD_SRST_N	D	Q _{n+1}
0	Х	X	Х	Х	0
1	Not rising	Х	Х	Х	Q _n
1	\uparrow	0	Х	Х	Q _n
1	\uparrow	1	0	Х	0
1	\uparrow	1	1	D	D

Table 1-1. RD Register Truth Table



2. Internal Configurator Connections (Ask a Question)

This chapter describes an example where a Two-Port LSRAM configuration generates a component with the following address widths.

- WADDR[*WA_MSB:0*]
- RADDR[RA_MSB:0]

In this example, assume the following:

- *M* is the width of the address on the write-port of each LSRAM block.
- *N* is the width of the address on the read-port of each LSRAM block.
- The decoder logic function is *decode*(addr[*j*:*k*], *i*), where 0 <= *i* < 2^(j-k+1).
- *D* is the depth of an LSRAM block in the array of blocks, starting at 0.

LSRAM Block Port Depth x Width	<i>M, N</i>
2Kx9	11
1Kx18	10

2.1 WEN Connections (Ask a Question)

The **WEN** signal on the generated component is connected to the write port block select input (**B_BLK**) for each LSRAM block according to the block depth within the component and synchronized with **WCLK**.

Table 2-1. WEN Connections

Depth	B_BLK[2]	B_BLK[1]	B_BLK[0]
WA_MSB < N	WEN	1	0
WA_MSB = N	WEN	1	decode(WADDR[M:M],D%2)
<i>WA_MSB</i> = <i>M</i> +1	WEN	decode (WADDR [<i>M</i> +1: <i>M</i> +1], (<i>D</i> /2)%2)	decode (WADDR [<i>M</i> : <i>M</i>], <i>D</i> %2)
<i>WA_MSB</i> > <i>M</i> +1	WEN & decode (WADDR[WA_MSB:M+2], D/4)	decode (WADDR [<i>M</i> +1: <i>M</i> +1], (<i>D</i> /2)%2)	decode (WADDR[M:M], D%2)

2.2 REN Connections (Ask a Question)

The **REN** signal on the generated component is connected to the write port block select input (**A_BLK**) for each LSRAM block according to the block depth within the component and synchronized with **RCLK**.

Table 2-2. REN Connections

Depth	A_BLK[2]	A_BLK[1]	A_BLK[0]	A_REN	Read- Data when REN=0
RA_MSB < N	1	1	1	REN	Hold
RA_MSB = N	REN	1	decode(RADDR [N:N], D%2)	1	0
<i>RA_MSB</i> = <i>N</i> +1	REN	decode(RADDR [<i>N</i> +1: <i>N</i> +1], (<i>D</i> / 2)%2)	decode (RADDR [N:N], D%2)	1	0
<i>RA_MSB</i> > <i>N</i> +1	REN & decode(RADDR[RA_MSB:N+2], D/4)	decode(RADDR [N+1:N+1], (D/ 2)%2)	decode (RADDR [<i>N:N</i>], <i>D</i> %2)	1	0



Notes: Observe the different behaviors when **REN** is de-asserted on the top-level generated component:

- If there is no depth cascading (*RA_MSB < N*), de-asserting **REN** holds the previously read-data.
- If there is depth cascading (*RA_MSB* >= *N*), de-asserting **REN** generates zeros on the read-data.

The different behavior in these two scenarios occurs because the component's **REN** input is used to drive either the LSRAM block's **A_REN** input or the read-port block select input (**A_BLK**), depending on the cascading configuration.

2.3 WD Connections (Ask a Question)

The **WD** bits on the generated component are partitioned into slices based on the width of the data on the write port of each LSRAM block. Each bit of **WD** is connected to all blocks in a slice at every depth and synchronized with **WCLK**.

2.4 RD Logic (Ask a Question)

The **RD** bits on the generated component are partitioned into slices based on the width of the data on the read port of each LSRAM block. Each bit of read-data from all blocks in a slice at every depth is OR'd together to generate a bit of **RD**. The **RD** bits are synchronized with **RCLK** according to the latency in the following table.

ECC Pipeline	ECC	RD Pipeline	RD Latency
No	No	No	0
No	No	Yes	1
No	Yes	No	0
No	Yes	Yes	1
Yes	Yes	No	1
Yes	Yes	Yes	2

Table 2-3. RD Logic Latencies

2.5 SB_CORRECT and DB_DETECT Logic (Ask a Question)

The **SB_CORRECT** and **DB_DETECT** outputs are synchronized with **RCLK** according to the above **RD** latency.

The **SB_CORRECT** flags of each LSRAM block are gated by the block's **A_BLK** signals that are pipelined one more than the **RD** latency value, and then OR'd together to generate the **SB_CORRECT** output of the component.

Similarly, the **DB_DETECT** flags of each LSRAM block are gated by the block's **A_BLK** signals that are pipelined one more than the **RD** latency value, and then OR'd together to generate the **DB_DETECT** output of the component. As a result, both the outputs are zero whenever **REN** is de-asserted.



3. Caveats for Two-Port Large SRAM Generation (Ask a Question)

- The core configurator supports depth cascading of up to 32 blocks only.
- The software returns a configuration error for unsupported configurations.
- All unused inputs must be grounded. ARST_N resets only the pipeline register for RD; it does not reset the memory contents.
- Writing to and reading from the same address is undefined and should be avoided.
- Although there is no collision prevention or detection, correct data is expected to be written into the memory.



4. Supported Formats (Ask a Question)

The following sections describe the supported memory file formats.

4.1 Intel HEX (Ask a Question)

Intel HEX is a standard file format created by Intel. Intel HEX files end with a HEX or IHX extension (for example, file2.hex or file3.ihx).

Memory contents are stored in ASCII files using hexadecimal characters. Each file contains a series of records (lines of text) delimited by new line, '\n', characters and each record starts with a ':' character. For more information about this format, see the *Intel HEX Record Format Specification* document on the web (search for Intel Hexadecimal Object File for several examples).

The Intel HEX record is composed of five fields arranged as follows:

:llaaaatt[dd...]cc

Where:

- : is the start code of every Intel HEX record.
- 11 is the byte count of the data field.
- aaaa is the 16-bit address of the beginning of the memory position for the data. Address is big Endian.
- tt is the record type that defines the data field:
 - 00 data record
 - 01 end of file record
 - 02 extended segment address record
 - 03 start segment address record (ignored by Microchip SoC tools)
 - 04 extended linear address record
 - 05 start linear address record (ignored by Microchip SoC tools)
- [dd...] is a sequence of *n* bytes of the data (*n* is equivalent to what was specified in the 11 field).
- cc is a checksum of count, address, and data. The following is an example of an Intel HEX record: :0300300002337A1E

Note: Configurator organizes data according to big Endian sequence. Intel HEX format requires byte-aligned port widths (for more information, see section 4.3. Write Port Width Alignment).

4.2 Motorola S-Record (Ask a Question)

Motorola S-Records use the file extension S (for example, file4.s).

Similar to Intel HEX, Motorola S-records use ASCII files, hex characters, and records to specify memory content. For more information about this format, search the web for several examples of the Motorola S-record description document. The RAM Content Manager uses only the S1 through S3 record types and ignores other record types.

The key difference between Intel HEX and Motorola S-record types is the record format, along with the extra error-checking features incorporated into Motorola S.

In both formats, memory content is specified by providing a starting address and a data set. The upper bits of the data set are loaded into the starting address and leftovers overflow into the adjacent addresses until the entire data set is used.



The Motorola S-record is composed of six fields and arranged as follows:

Stllaaaa[dd...]cc

Where:

- s is the start code of every Motorola S-record.
- t is the record type that defines the data field.
- 11 is the byte count of the data field.
- aaaa is a 16-bit address of the beginning of the memory position for the data. Address is big Endian.
- [dd...] is a sequence of *n* bytes of the data where *n* is equivalent to what was specified in the 11 field.
- cc is the checksum of count, address, and data. The following is an example of a Motorola S-record:

S10a0000112233445566778899FFFA

Note: Configurator organizes data according to big Endian sequence. Motorola-S format requires byte-aligned port widths (for more information, see section 4.3. Write Port Width Alignment).

4.3 Write Port Width Alignment (Ask a Question)

The Microchip implementation of these formats interprets data sets in bytes. The implementation used is the same for all memory formats. The following examples show how data in a memory file is interpreted for different write port widths of memory.

The following figure shows data in Intel HEX memory file format. The same data is assumed to be used to initialize RAM in all examples.

Figure 4-1. Memory File Data - Intel HEX Memory File Format



The Hex data from the memory file is converted into binary and read by the tool as a stream of bits. Based on the memory port width, the *required number of bits* for each address location in RAM is taken from the stream of bits.

Note: The *required number of bits* taken from the stream of bits for each address location is always a multiple of 8 (byte).

4.3.1 Write Port Widths Aligned on Byte Boundary (Ask a Question)

The following examples show how data from a memory file is stored in RAM when memory port widths are a multiple of a byte (aligned on a byte boundary).

4.3.1.1 32-bit Write Port Width (Ask a Question)

When the memory write port width is 32 bits, which is aligned on a byte boundary, the tool uses 32 bits from the binary stream for each 32-bit word in the RAM. The resulting data stored in RAM is shown in the following figure.



Figure 4-2. Data in RAM - 32-bit Write Port Width Aligned on Byte Boundary

Memory File Data	Address	Data Stored in RAM
:04000000FF11EE22DC	0	0x <mark>22EE11FF</mark>
:04000400DD33CC44D8	1	0x44CC33DD
:04000800 <mark>BB550012</mark> D2	2	0x <mark>120055BB</mark>

4.3.1.2 16-bit Write Port Width (Ask a Question)

When the memory write port width is 16 bits, which is aligned on a byte boundary, the tool uses 16 bits from the binary stream for each 16-bit word in the RAM. The resulting data stored in RAM is shown in the following figure.

Figure 4-3. Data in RAM - 16-bit Write Port Width Aligned on Byte Boundary

Memory File Data	Address	Data Stored in RAM
4000000 <mark>FF11EE22</mark> DC	0	0x <mark>11FF</mark>
000400 <mark>DD33CC44</mark> D8	1	0x <mark>22EE</mark>
000800 <mark>BB550012</mark> D2	2	0x <mark>33DD</mark>
	3	0x <mark>44CC</mark>
	4	0x <mark>55BB</mark>
	5	0x <mark>1200</mark>

4.3.1.3 8-bit Write Port Width (Ask a Question)

When the memory write port width is 8 bits, which is aligned on a byte boundary, the tool uses 8 bits from the binary stream for each 8-bit word in the RAM. The resulting data stored in RAM is shown in the following figure.



Figure 4-4. Data in RAM - 8-bit Write Port Width Aligned on Byte Boundary

Memory File Data	
:04000000 <mark>FF11EE22</mark> DC	
:04000400 <mark>0033CC44</mark> D8	
:04000800 BB550012 D2	

Address	Data Stored in RAM
0	0x <mark>FF</mark>
1	0x <mark>11</mark>
2	0x <mark>EE</mark>
3	0x <mark>22</mark>
4	0x <mark>DD</mark>
5	0x <mark>33</mark>
6	0x <mark>CC</mark>
7	0x <mark>44</mark>
8	0x <mark>BB</mark>
9	0x <mark>55</mark>
А	0x <mark>00</mark>
В	0x <mark>12</mark>

4.3.2 Write Port Widths Not Aligned on Byte Boundary (Ask a Question)

The following examples show how data from a memory file is stored in RAM when memory port widths are not a multiple of a byte.

4.3.2.1 9-bit Write Port Width (Ask a Question)

When the memory write port width is 9 bits, which is not aligned on a byte boundary, the tool uses 16 bits from the binary stream for each 9-bit word. The tool ignores the upper 7 bits of each 16 bits when processing the memory file data. The resulting data stored in RAM is shown in the following figure.

Figure 4-5. Data in RAM - 9-bit Write Port Width Not Aligned on Byte Boundary

Memory File Data
:04000000FF11EE22DC
:04000400 <mark>DD33CC44</mark> D8
:04000800 <mark>BB550012</mark> D2

Address	Data Stored in RAM
0	0x <mark>1FF</mark>
1	0x <mark>0EE</mark>
2	0x <mark>1DD</mark>
3	0x <mark>0CC</mark>
4	0x <mark>1BB</mark>
5	0x <mark>000</mark>

4.3.2.2 4-bit Write Port Width (Ask a Question)

When the memory write port width is 4 bits, which is not aligned on a byte boundary, the tool uses 8 bits from the binary stream for each 4-bit word. The tool ignores the upper 4 bits of each 8 bits when processing the memory file data. The resulting data stored in RAM is shown in the following figure.



Figure 4-6. Data in RAM - 4-bit Write Port Width Not Aligned on Byte Boundary

Memory File Data
:04000000 <mark>FF11EE22</mark> DC
:04000400 <mark>DD33CC44</mark> D8
:04000800 <mark>BB</mark> 550012D2

Address	Data Stored in RAM
0	0x <mark>f</mark>
1	0x <mark>1</mark>
2	0x <mark>E</mark>
3	0x <mark>2</mark>
4	0x <mark>D</mark>
5	0x <mark>3</mark>
6	0x <mark>C</mark>
7	0x <mark>4</mark>
8	0x <mark>B</mark>
9	0x <mark>5</mark>
A	0x <mark>0</mark>
В	0x <mark>2</mark>

4.3.3 Specifying Data in Memory File (Ask a Question)

If all the bits in the memory file are relevant, take steps to avoid bits from being ignored when the write port width is not aligned on a byte boundary. The following examples describe how to specify data in memory file so that the tool does not ignore bits. To avoid bits from being ignored, convert the hexadecimal data intended to initialize RAM into binary stream of bits, and then pad (insert) zeros based on the port width so that resulting data is byte-aligned, as described in the following sections.

4.3.3.1 9-bit Write Port Width (Ask a Question)

Consider the following Intel HEX memory file.

Figure 4-7. Memory File Data - Intel HEX Memory File

:0400000FF11EE22DC
:04000400D33CC44D8
:04000800BB550012D2

The binary stream of bits for above memory file data is:

0001 0010 0000 0000 0101 0101 1011 1011 0100 0100 1100 1100 0011 0011 1101 1101 0010 0010 1110 1110 0001 0001 1111 1111

If the memory port width is 9 bits, you must pad 7 zeros to every 9 bits of data from the binary stream to create 16 bits (byte-aligned), as shown in the following figure.



Figure 4-8. Padding Zeros to Create 16 Bits



The following figure shows the equivalent memory file data padded with zeros to achieve a 9-bit write port width.

Figure 4-9. Equivalent Memory File Data Padded with Zeros (9-bit Write Port Width)

:04000000 <mark>FF010801</mark> F3	
:04000400 <mark>BB00A401</mark> 98	
:040008003D01610055	
:04000c001301760165	
:040010005500 <mark>0001</mark> 96	
:04001400 <mark>0400</mark> 0000E4	

When the tool parses the above memory file data (padded with zeros), the tool converts the data to binary and reads it as a stream of bits. If the port width is 9 bits, the tool reads 16 bits (byte-aligned), ignores the upper 7 bits, and stores the lower 9 bits of actual data in RAM, as shown in the following table.



Address	Data
0	Ox1FF
1	0x108
2	0x0BB
3	0x1A4
4	0x13D
5	0x061
6	0x113
7	0x176
8	0x055
9	0x100
A	0x004
В	0x000

4.3.3.2 4-bit Write Port Width (Ask a Question)

Consider the following Intel HEX memory file.



Figure 4-10. Memory File Data - Intel HEX Memory File



The binary stream of bits for above memory file data is:

0001 0010 0000 0000 0101 0101 1011 1011 0100 0100 1100 1100 0011 0011 1101 1101 0010 0010 1110 1110 0001 0001 1111 1111

If the memory port width is 4 bits, the tool reads 8 bits at a time from the binary stream above. For the 8 bits, you must pad zeros for the upper 4 bits and specify the actual data in the lower 4 bits, as shown in the following figure.

Figure 4-11. Padding Zeros for the Upper 4 Bits and Specifying Data in the Lower 4 Bits



The following figure shows the equivalent memory file data padded with zeros to achieve a 4-bit write port width.

Figure 4-12. Equivalent Memory File Data Padded with Zeros (4-bit Write Port Width)

:04000000 <mark>0F0F</mark> 0101DC
:040004000E0E <mark>0202</mark> D8
:040008000D0D0303D4
:04000c000c0c0404D0
:040010000B0B0505cc
:0400140000 <mark>0002</mark> 01E5

When the tool parses the above memory file data (padded with zeros), it converts the data to binary and reads it as a stream of bits. If the port width is 4 bits, the tool reads 8 bits (byte-aligned), ignores the upper 4 bits of actual data, and stores the lower 4 bits of actual data in RAM, as shown in the following table.

Table 4-2. 16-bit Write Port Width

Address	Data
0	OxF
1	0xF



continued	
Address	Data
2	0x1
3	0x1
4	OxE
5	OxE
6	0x2
7	0x2
8	0xD
9	OxD
A	0x3
В	0x3
C	0xC
D	0xC
E	0x4
F	0x4
10	0xB
11	0xB
12	0x5
13	0x5
14	0x0
15	0x0
16	0x2
17	0x1

Note: x1 and x2 port widths are handled using the same technique of padding zeros. You always zero pad to the next 8-bit-width increment (8, 16, 24, and so on). If a write port width is not aligned on a byte boundary, the following message appears.

Figure 4-13. Message when a Write Port Width is Not Aligned on a Byte Boundary

Сезинтнегания	Configure Two-port Large SRAM
Dease sel	
INFO: Write Port width is not aligned on byte boundary. Please refer	Optimized for High Speed Low Power Initialize RAM for Simulation Customize RAM Content to the Supported Memory Formats section in RTG4 FPGA Two - Port Large SRAM Configuration User Guide for more details WD [17.0] Depth: [1024 WADDR [9.0] Wdth: [18 [17.0] RD Read Po RADDR [9.0] Depth: [1024 RaDDR
Files Design Flow Catalog Stimulus Hierarchy	RD_SRST Expose Write Byte Enab EC(Disabled I ARST_N)



5. RAM Content Manager (Ask a Question)

The RAM Content Manager allows you to specify the contents of your memory in a way that avoids the simulation cycles required for initializing the memory, thereby reducing simulation runtime.

The RAM core generator removes much of the complexity required to generate large memory that uses one or more RAM blocks on the device. It does so by using one or more memory blocks to generate a RAM matching your configuration, while creating the surrounding cascading logic.

The configurator cascades RAM blocks three ways:

- Cascaded deep (for example, 2 blocks of 1024x18 to create a 2048x18)
- Cascaded wide (for example, 2 blocks of 1024x18 to create a 1024x36)
- Cascaded wide and deep (for example, 4 blocks of 1024x18 to create a 2048x36, in a 2 blocks width-wise by 2 blocks depth-wise configuration)

Using the configurator, you specify memory content in terms of your total memory size. The configurator partitions your memory file so that content is directed to the appropriate block RAM when multiple blocks are cascaded.

5.1 Opening and Using RAM Content Manager (Ask a Question)

The following sections describe how to open and use the RAM Content Manager.

5.1.1 Opening RAM Content Manager (Ask a Question)

To open RAM Content Manager:

- 1. Specify your RAM configuration by setting your Read and Write Depth and Width.
- 2. Select the Initialize RAM for Simulation check box.

3. Click **Customize RAM Content**. The SRAM Content Manager appears, as shown in the following figure.



/rite Port C Depth	4 Read Port A Dep	th 64
/rite Port C Width	8 Read Port A Widt	th 18
/rite Port C View Read F	ort A View	
Go To Address: 0	Go	
Address DEC	Data HEX 💌	
	0	00000
	1	00000
	2	00000
	3	00000
	4	00000
		00000
	7	00000
	8	00000
	9	00000
1	0	00000
1	1	00000
1	2	00000
1	3	00000
1	4	00000
1	5	00000
1	6	00000
1	7	00000
1 1	B Default Value Data	00000
	Delauk value Data ju	

Figure 5-1. Customize SRAM Content for Simulation



Important:

- 1. Clearing and selecting the **Initialize RAM for Simulation** check box in the same dialog box does not discard the memory file data in the generated files. To discard the memory file data, clear the **Initialize RAM for Simulation** check box and click **OK**.
- 2. After selecting the **Initialize RAM for Simulation** check box, use the **Customize RAM Content** option to initialize memory content to zeros.

5.1.2 RAM Configuration (Ask a Question)

The following table lists the RAM configuration.



Table 5-1. RAM Configuration

RAM Configuration	Description
Write Port Depth	As specified in the RAM core generator dialog box (not editable).
Write Port Width	As specified in the RAM core generator dialog box (not editable).
Read Port Depth	As specified in the RAM core generator dialog box (not editable).
Read Port Width	As specified in the RAM core generator dialog box (not editable).

5.1.3 Write Port View and Read Port View (Ask a Question)

The following table lists the Write Port and Read Port Views.

Write Port and Read Port Views	Description
Go To Address	Allows you to go to a specific address in the manager. Each memory block has many addresses; it is often difficult to scroll through and find a specific one. This task is simplified by allowing you to type a specific address. The number display format (Hex, Bin, Dec) is controlled by the value you set in the drop-down menu above the Address column.
Address	The Address column lists the address of a memory location. The drop-down menu specifies the number format for your address list (hexadecimal, binary, or decimal).
Data	Allows you to control the data format and data value in the manager. Click the value to change it. Note: Dialogs show all data with the MSB down to the LSB. For example, if the row shows 0xAABB for a 16-bit word size, the MSB would be AA and the LSP would be BB.
Default Data Value	The value given to memory addresses that have not been explicitly initialized by importing content or editing manually. When changed, all default values in the manager are updated to match the new value. The number display format (Hex, Bin, Dec) is controlled by the value you set in the drop-down menu above the Data column.
Reset All Values	Resets the Data values.
Import from File	Opens the Import Memory Content dialog box; enables you to select a memory content file (Intel HEX) to load. Intel HEX file extensions are set to $*.hex$ during import.
ОК	Closes the manager and saves all the changes made to the memory and its contents.
Cancel	Closes the manager, cancels all your changes in this instance of the manager, and returns the memory to the state it held before the manager was opened.

Table 5-2. Write Port and Read Port View

5.2 MEMFILE (RAM Content Manager Output File) (Ask a Question)

To transfer RAM data from the RAM Content Manager to test equipment, use MEM files. RAM contents are first organized into the logical layer, and then reorganized to fit the hardware layer. Then the contents are stored in MEM files that are read by other systems and used for testing.

The MEM files are named according to the logical structure of RAM elements created by the configurator. Using this method, the highest order RAM blocks are named CORE_ROC0.mem, where "R" stands for row and "C" stands for column. For multiple RAM blocks, the naming continues with CORE_ROC1, CORE_ROC2, CORE_R1C0, and so on.

Data intended for RAM is stored as ASCII 1s and 0s within the file. Each memory address occupies one line. Words from logical layer blocks are concatenated or split to make them fit efficiently within the hardware blocks. If the logical layer width is less than the hardware layer, two or more logical layer words are concatenated to form one hardware layer word. In this case, the lowest bits of the hardware word comprise the lower address data bits from the logical layer. If the logical layer width exceeds the hardware layer, the words are split, with the lower bits placed in lower addresses.



If the logical layer words do not fit cleanly into the hardware layer words, the most significant bit of the hardware layer words is not used and defaults to zero. This is also done when the logical layer width is 1 to avoid left over memory at the end of the hardware block.



6. Port Description (Ask a Question)

The following table lists the Two-Port Large SRAM signals in the generated macro.

Port	Direction	Default Polarity	Description
CLK	In	Rising Edge	Single clock to drive both WCLK and RCLK.
WD[]	In	—	Write data.
WADDR[]	In	_	Write address.
WEN	In	Active-high	Write port enable.
WCLK	In	Rising edge	Write clock.
RCLK	In	Rising edge	Read clock.
REN	In	Active-high	Read data enable.
RADDR[]	In	—	Read address.
RD[]	Out	_	Read data.
RD_EN	In	Active-high	Read data register enable.
RD_SRST_N	In	Active-low	Read data register Synchronous reset.
ARST_N	In	Active-low	Read data register Asynchronous reset.
SB_CORRECT	Out	Active-high	Single-bit correct flag.
DB_DETECT	Out	Active-high	Double-bit detect flag.
WBYTE_EN[]	In	Active-high	Write Byte Enables (per byte).

Table 6-1. Two-Port Large SRAM Signals



7. Parameters (Ask a Question)

The following table lists the Two-Port Large SRAM parameters in the generated macro.

Parameter	Valid Range	Default (Condition)	Description
LPMTYPE	LPM_RAM	LPM_RAM	Macro category.
PTYPE	1, 2	1	1: Two-port.
			2: Dual-port.
INIT_RAM	F, T	F	F: No RAM initialization for simulation. T: Initialize RAM for simulation.
IMPORT_FILE	-	IMPORT_FILE Dummy parameter (INIT_RAM=T)	Memory file to be imported to initialize RAM. No Tcl support yet
CASCADE	0, 1	0	0: Cascading for WIDTH or Speed. 1: Cascading for DEPTH or Power.
CLKS	1, 2	1	1: Single Read/Write clock. 2: Independent Read and Write clocks.
CLOCK_PN	CLK CLK_N	CLK (CLKS=1)	Single clock Port name.
CLK_EDGE	RISE, FALL	RISE (CLKS=1)	RISE: Rising edge Single clock. FALL: Falling edge Single clock.
WCLOCK_PN	WCLK WCLK_N	WCLK (CLKS=2)	Write clock Port name
RCLOCK_PN	RCLK RCLK_N	RCLK (CLKS=2)	Read clock Port name.
WCLK_EDGE	RISE, FALL	RISE (CLKS=2)	RISE: Rising edge Write clock. FALL: Falling edge Write clock.
RCLK_EDGE	RISE, FALL	RISE (CLKS=2)	RISE: Rising edge Read clock. FALL: Falling edge Read clock.
WWIDTH	1-7524	18	Write data width.
WDEPTH	1-65536	1024	Write address depth.
RWIDTH	1-7524	18	Read data output width.
RDEPTH	1- 65536	1024	Read address depth.
WE_POLARITY	0, 1, 2	1	0: Active-low W_EN_N port will be exposed to exercise Write port enable.
			be exposed to exercise Write port enable.
			2: Write port enable tied off to be always active.

 Table 7-1.
 Two-Port Large SRAM Parameters



continued				
Parameter	Valid Range	Default (Condition)	Description	
WE_PN	WEN WEN_N	WEN	Write port enable Port name.	
RE_POLARITY	0, 1, 2	2	0: Active-low R_EN_N port will be exposed to exercise Read port enable.	
			1: Active-high R_EN port will be exposed to exercise Read port enable.	
			2: Read port enable tied off to be always active.	
RE_PN	REN REN_N	REN	Read port enable Port name.	
RPMODE	0, 1	0	0: Bypass Read data register. 1: Pipeline Read data.	
DATA_OUT_PN	—	RD	Read data Port name.	
A_DOUT_EN_POLARITY	0, 1, 2	2 (RPMODE =1)	0: Active-low A_DOUT_EN_N port will be exposed to exercise Port A read data register enable.	
			1: Active-high A_DOUT_EN port will be exposed to exercise Port A read data register enable.	
			2: Port A read data register enable tied off to be always active.	
A_DOUT_EN_PN	RD_EN RD_EN_N	RD_EN (RPMODE =1)	Read data register enable Port name.	
A_DOUT_SRST_POLARITY	0, 1, 2	2 (RPMODE =1)	0: Active-low A_DOUT_SRST_N port will be exposed to exercise Port A read data register Sync-reset	
			1: Active-high A_DOUT_SRST port will be exposed to exercise Port A read data register Sync-reset	
			2: Port A read data register Sync- reset tied off to be always inactive.	
A_DOUT_SRST_PN	RD_SRST RD_SRST_N	RD_SRST_N (RPMODE =1)	Read data register Sync-reset Port name.	
ARST_N_POLARITY	0, 1, 2	2 (RPMODE =1)	Asynchronous Reset Polarity 0: Active-low ARST_N port will be exposed to exercise Read data register Async reset 1: Active-high ARST port will be exposed to exercise Read data register Async reset	
			2: Read data register Async- reset tied off to be always inactive	



continued			
Parameter	Valid Range	Default (Condition)	Description
RESET_PN	ARST_N ARST	ARST_N (RPMODE =1)	Read data register Async- reset Port name.
ECC	0, 1, 2	0	0: ECC disabled. 1: ECC Pipelined. 2: ECC Non-pipelined.
DATA_IN_PN	_	WD	Write data Port name.
WADDRESS_PN	-	WADDR	Write address Port name.
RADDRESS_PN	_	RADDR	Read address Port name.
BYTEENABLES	0, 1	0	0: Do not generate WBYTE_EN. 1: Generate WBYTE_EN.
A_WBYTE_EN_PN	-	WBYTE_EN	Write Byte enable port name
BYTE_ENABLE_WIDTH	_	0	Write port Byte Enable width Values are based on the configuration



8. Revision History (Ask a Question)

The revision history describes the changes that were implemented in the document. The changes are listed by revision, starting with the most current publication.

Revision	Date	Description
C	09/2023	Added a note about the Initialize RAM for Simulation option. See 5.1.1. Opening RAM Content Manager.
В	12/2021	Revised section 4. Supported Formats.
A	11/2020	Initial Revision



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